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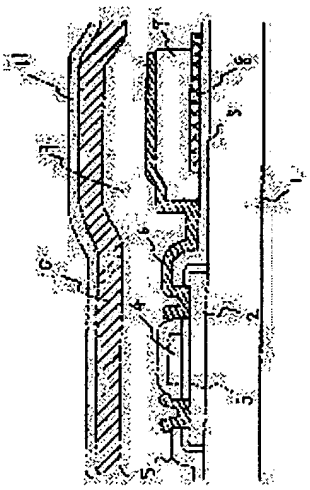
(54) SOLID-STATE IMAGE SENSING DEVICE

(57)Abstract:



PURPOSE: To manufacture the title device with excellent moisture resistance by a method wherein a three layered passivation structure is composed of a high temperature cured polyimide, a low temperature cured polyimide and an inorganic material.

CONSTITUTION: A photodetector comprising an amorphous silicon 2 and a thin film transistor formed of a gate oxide film 3 driving the photodetector, a polycrystalline silicon gate electrode 4, interlayer insulating films 5, an aluminium electrode 6, an a-Si:H 7 and a transparent electrode 8 are formed on an insulating substrate 1 to constitute a solid image pick-up device. Furthermore, a polyimide resin coating layer 9 to be cured at the temperature not exceeding 300°C and another polyimide resin coating layer 10 to be imidized at the temperature exceeding 300°C are formed on the topmost part and after curing these two kinds of polyimide resin coating layers at the temperature exceeding 150°C and not exceeding 300°C, the other coating layer 11 comprising an inorganic material is formed at the temperature not exceeding 300°C to provide a three layered passivation layer.

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